



THE DATASHEET OF STS1NK60Z





STS1NK60Z

N-CHANNEL 600V - 13Ω - 0.25A - SO-8
Zener-Protected SuperMESH™ Power MOSFET

| TYPE | V _{DSS} | R _{DS(on)} | I _D | P _w |
|-----------|------------------|---------------------|----------------|----------------|
| STS1NK60Z | 600 V | < 15 Ω | 0.25 A | 2 W |

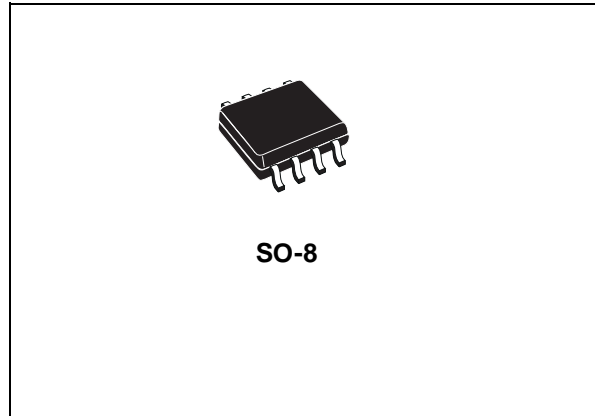
- TYPICAL R_{DS(on)} = 13Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- ESD IMPROVED CAPABILITY
- 100% AVALANCHE TESTED
- NEW HIGH VOLTAGE BENCHMARK
- GATE CHARGE MINIMIZED

DESCRIPTION

The SuperMESH™ series is obtained through an extreme optimization of ST's well established strip-based PowerMESH™ layout. In addition to pushing on-resistance significantly down, special care is taken to ensure a very good dv/dt capability for the most demanding applications. Such series complements ST full range of high voltage MOSFETs including revolutionary MDmesh™ products.

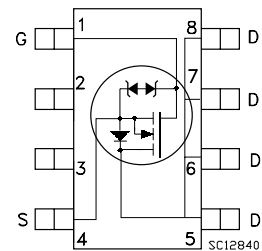
APPLICATIONS

- AC ADAPTORS AND BATTERY CHARGERS
- SWITCH MODE POWER SUPPLIES (SMPS)



SO-8

INTERNAL SCHEMATIC DIAGRAM



ORDERING INFORMATION

| SALES TYPE | MARKING | PACKAGE | PACKAGING |
|------------|---------|---------|-------------|
| STS1NK60Z | S1NK60Z | SO-8 | TAPE & REEL |

STS1NK60Z

ABSOLUTE MAXIMUM RATINGS

| Symbol | Parameter | Value | Unit |
|-----------------------|--|------------|------|
| V _{DS} | Drain-source Voltage (V _{GS} = 0) | 600 | V |
| V _{DGR} | Drain-gate Voltage (R _{GS} = 20 kΩ) | 600 | V |
| V _{GS} | Gate- source Voltage | ± 30 | V |
| I _D | Drain Current (continuous) at T _C = 25°C | 0.25 | A |
| I _D | Drain Current (continuous) at T _C = 100°C | 0.16 | A |
| I _{DM} (•) | Drain Current (pulsed) | 1 | A |
| P _{TOT} | Total Dissipation at T _C = 25°C | 2 | W |
| | Derating Factor | 0.016 | W/°C |
| V _{ESD(G-S)} | Gate source ESD(HBM-C=100pF, R=1.5KΩ) | 800 | V |
| dv/dt (1) | Peak Diode Recovery voltage slope | 4.5 | V/ns |
| T _j | Operating Junction Temperature | -55 to 150 | °C |
| T _{stg} | Storage Temperature | -55 to 150 | °C |

(•) Pulse width limited by safe operating area

(1) I_{SD} ≤ 0.3A, di/dt ≤ 200A/μs, V_{DD} ≤ V_{(BR)DSS}, T_j ≤ T_{JMAX}.

THERMAL DATA

| | | | |
|----------------------|---|------|------|
| R _{thj-amb} | Thermal Resistance Junction-ambient Max | 62.5 | °C/W |
|----------------------|---|------|------|

GATE-SOURCE ZENER DIODE

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|-------------------|-------------------------------|-------------------------------------|------|------|------|------|
| BV _{GSO} | Gate-Source Breakdown Voltage | I _{GS} =± 1mA (Open Drain) | 30 | | | V |

PROTECTION FEATURES OF GATE-TO-SOURCE ZENER DIODES

The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

ELECTRICAL CHARACTERISTICS ($T_{CASE} = 25^{\circ}C$ UNLESS OTHERWISE SPECIFIED)
 ON/OFF

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|---------------|--|--|------|------|----------|--------------------|
| $V_{(BR)DSS}$ | Drain-source Breakdown Voltage | $I_D = 1 \text{ mA}, V_{GS} = 0$ | 600 | | | V |
| I_{DSS} | Zero Gate Voltage Drain Current ($V_{GS} = 0$) | $V_{DS} = \text{Max Rating}$ $V_{DS} = \text{Max Rating}, T_C = 125^{\circ}C$ | | | 1 50 | μA μA |
| I_{GSS} | Gate-body Leakage Current ($V_{DS} = 0$) | $V_{GS} = \pm 20V$ | | | ± 10 | μA |
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS} = V_{GS}, I_D = 50 \mu A$ | 3 | 3.75 | 4.5 | V |
| $R_{DS(on)}$ | Static Drain-source On Resistance | $V_{GS} = 10V, I_D = 0.4 \text{ A}$ | | 13 | 15 | Ω |

DYNAMIC

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|-------------------------------------|---|---|------|-------------------|------|----------------|
| $g_{fs} (1)$ | Forward Transconductance | $V_{DS} = V, I_D = 0.4 \text{ A}$ | | 0.5 | | S |
| C_{iss} C_{oss} C_{rss} | Input Capacitance Output Capacitance Reverse Transfer Capacitance | $V_{DS} = 25V, f = 1 \text{ MHz}, V_{GS} = 0$ | | 94 17.6 2.8 | | pF pF pF |
| $C_{oss \text{ eq.}} (3)$ | Equivalent Output Capacitance | $V_{GS} = 0V, V_{DS} = 0V \text{ to } 480V$ | | 11 | | pF |

SWITCHING ON

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|-------------------------------|--|--|------|-----------------|------|----------------|
| $t_{d(on)}$ t_r | Turn-on Delay Time Rise Time | $V_{DD} = 300V, I_D = 0.4 \text{ A}$ $R_G = 4.7\Omega, V_{GS} = 10 \text{ V}$ (Resistive Load see, Figure 3) | | 5.5 5 | | ns ns |
| Q_g Q_{gs} Q_{gd} | Total Gate Charge Gate-Source Charge Gate-Drain Charge | $V_{DD} = 480V, I_D = 0.8 \text{ A},$ $V_{GS} = 10V$ | | 4.9 1 2.7 | 6.9 | nC nC nC |

SWITCHING OFF

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|----------------------------------|---|---|------|------------------|------|----------------|
| $t_{d(off)}$ t_f | Turn-off Delay Time Fall Time | $V_{DD} = 300V, I_D = 0.4A$ $R_G = 4.7\Omega, V_{GS} = 10 \text{ V}$ (Resistive Load see, Figure 3) | | 13 28 | | ns ns |
| $t_r(V_{off})$ t_f t_c | Off-voltage Rise Time Fall Time Cross-over Time | $V_{DD} = 480V, I_D = 0.8A,$ $R_G = 4.7\Omega, V_{GS} = 10V$ (Inductive Load see, Figure 5) | | 28 12.5 48 | | ns ns ns |

SOURCE DRAIN DIODE

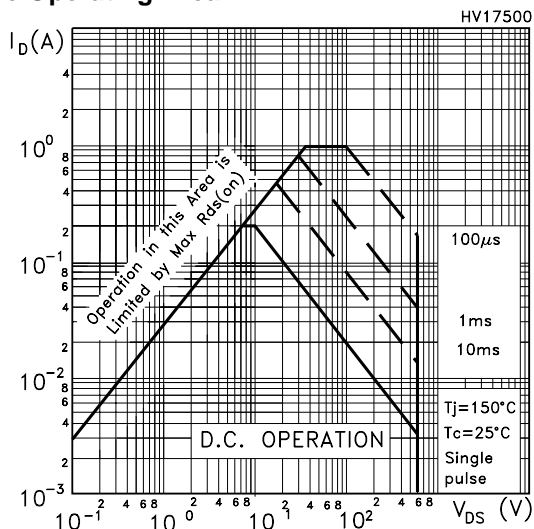
| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|-----------------------------------|--|--|------|-------------------|-----------|---------------|
| I_{SD} $I_{SDM} (2)$ | Source-drain Current Source-drain Current (pulsed) | | | | 0.25 1 | A A |
| $V_{SD} (1)$ | Forward On Voltage | $I_{SD} = 0.25A, V_{GS} = 0$ | | | 1.6 | V |
| t_{rr} Q_{rr} I_{RRM} | Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current | $I_{SD} = 0.8 \text{ A}, di/dt = 100A/\mu s$ $V_{DD} = 20V, T_j = 150^{\circ}C$ (see test circuit, Figure 5) | | 140 224 3.2 | | ns nC A |

 Note: 1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.

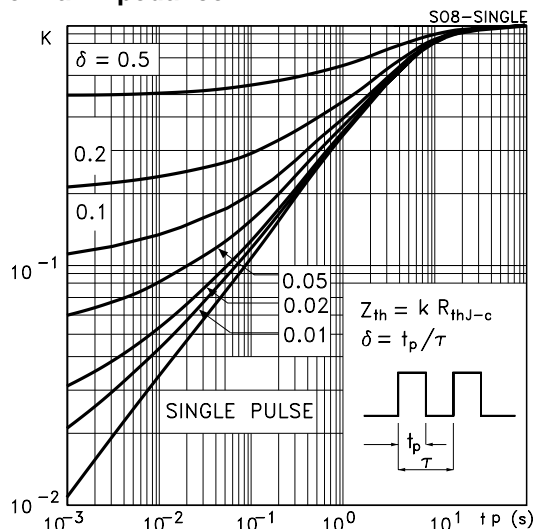
2. Pulse width limited by safe operating area.

 3. $C_{oss \text{ eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS} .

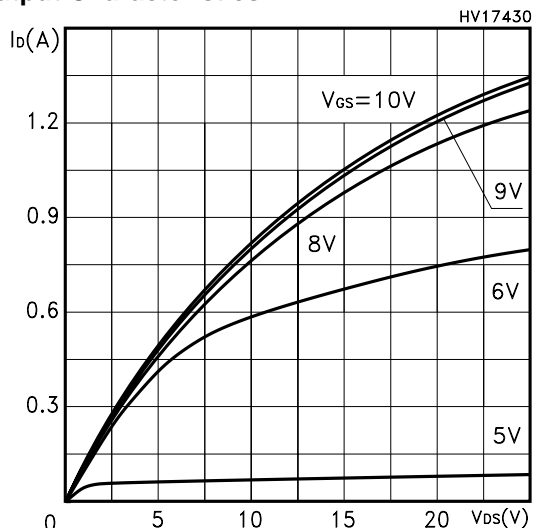
Safe Operating Area



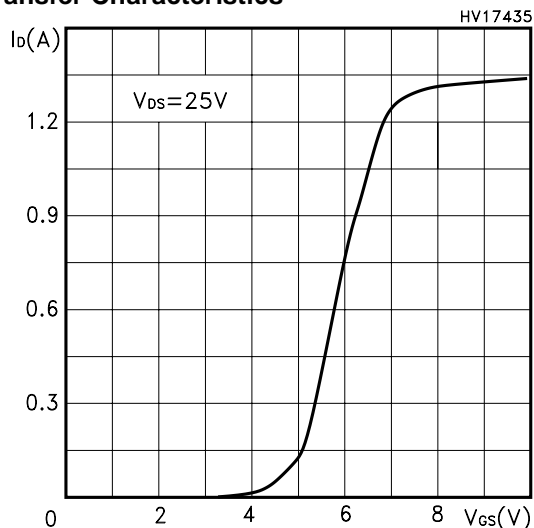
Thermal Impedance



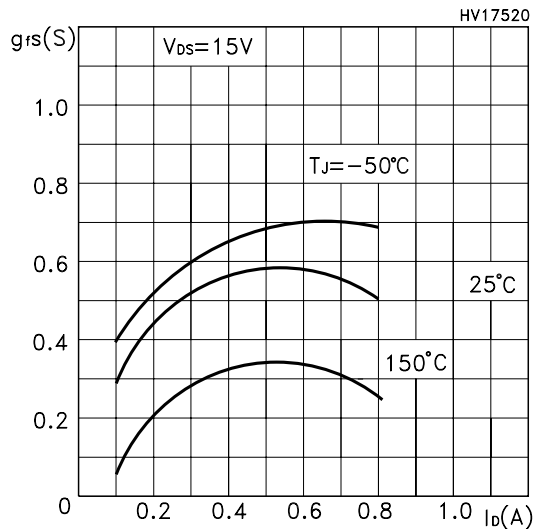
Output Characteristics



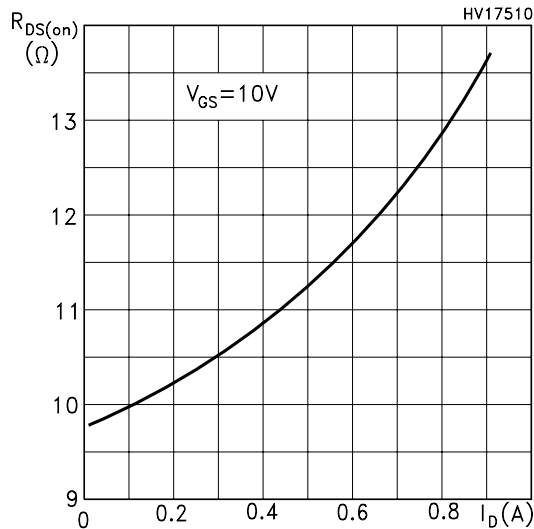
Transfer Characteristics



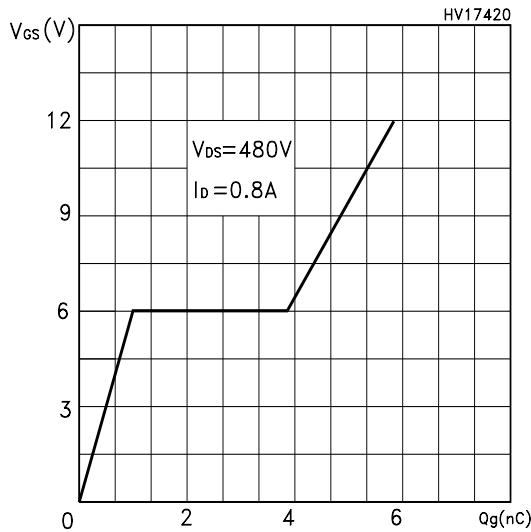
Transconductance



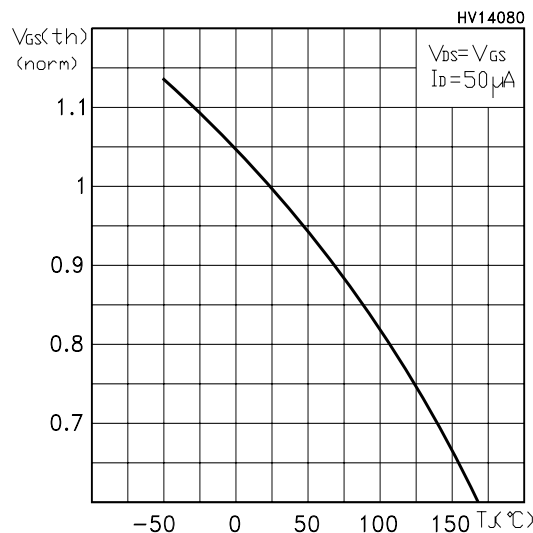
Static Drain-source On Resistance



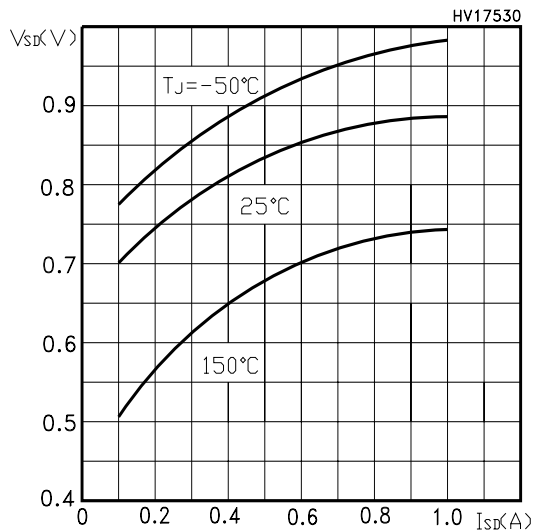
Gate Charge vs Gate-source Voltage



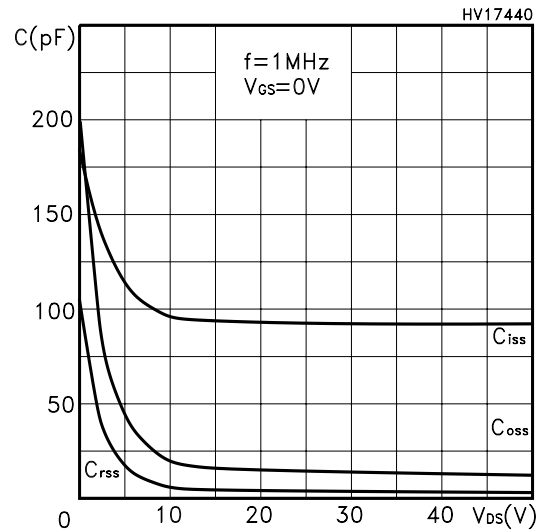
Normalized Gate Threshold Voltage vs Temp.



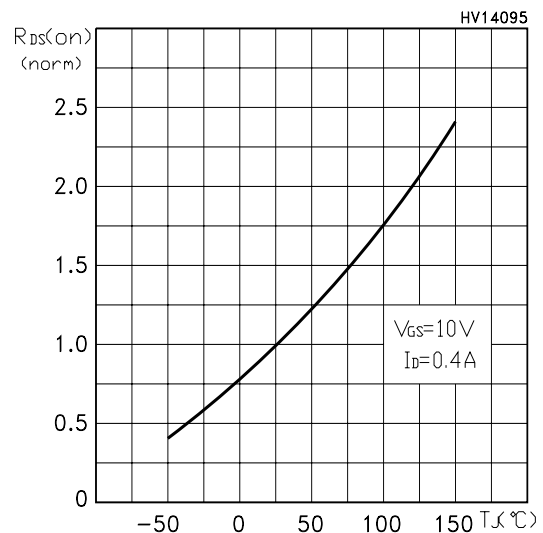
Source-drain Diode Forward Characteristics



Capacitance Variations



Normalized On Resistance vs Temperature



Normalized BVDSS vs Temperature

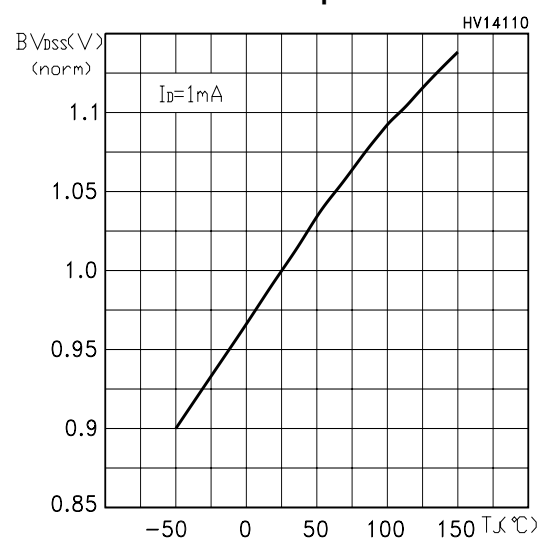


Fig. 1: Unclamped Inductive Load Test Circuit

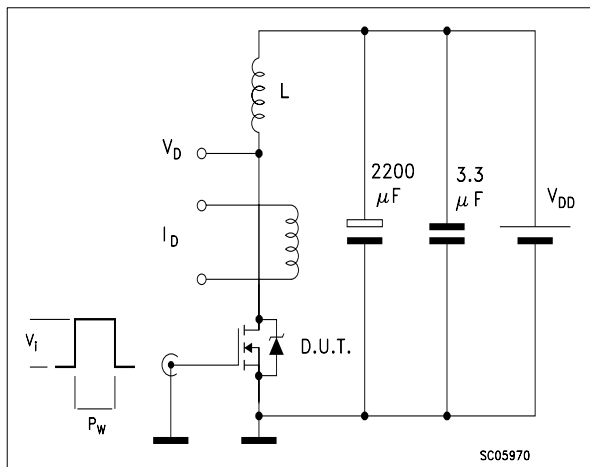


Fig. 2: Unclamped Inductive Waveform

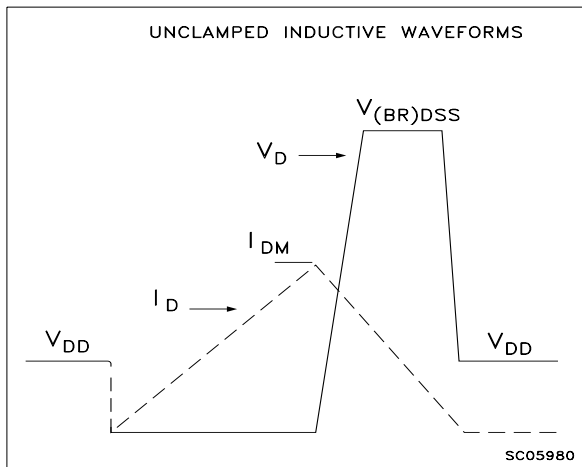


Fig. 3: Switching Times Test Circuit For Resistive Load

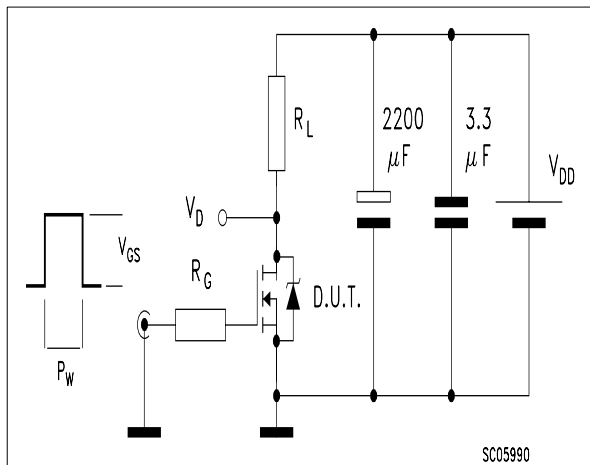


Fig. 4: Gate Charge test Circuit

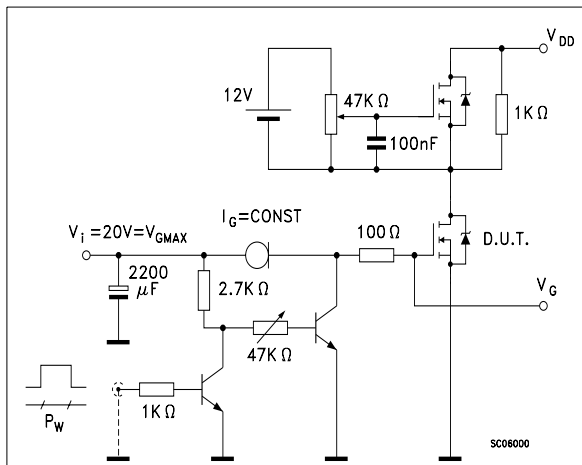
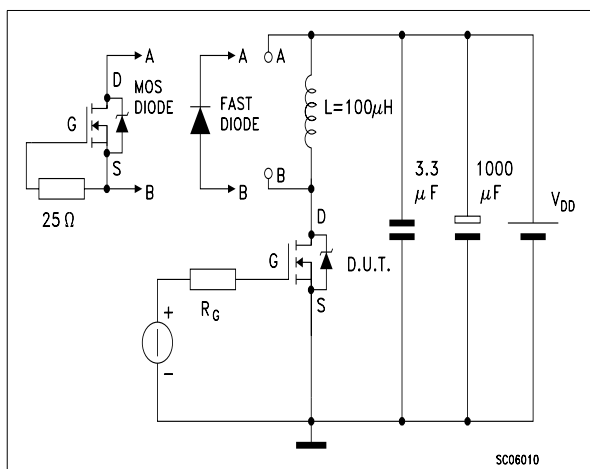
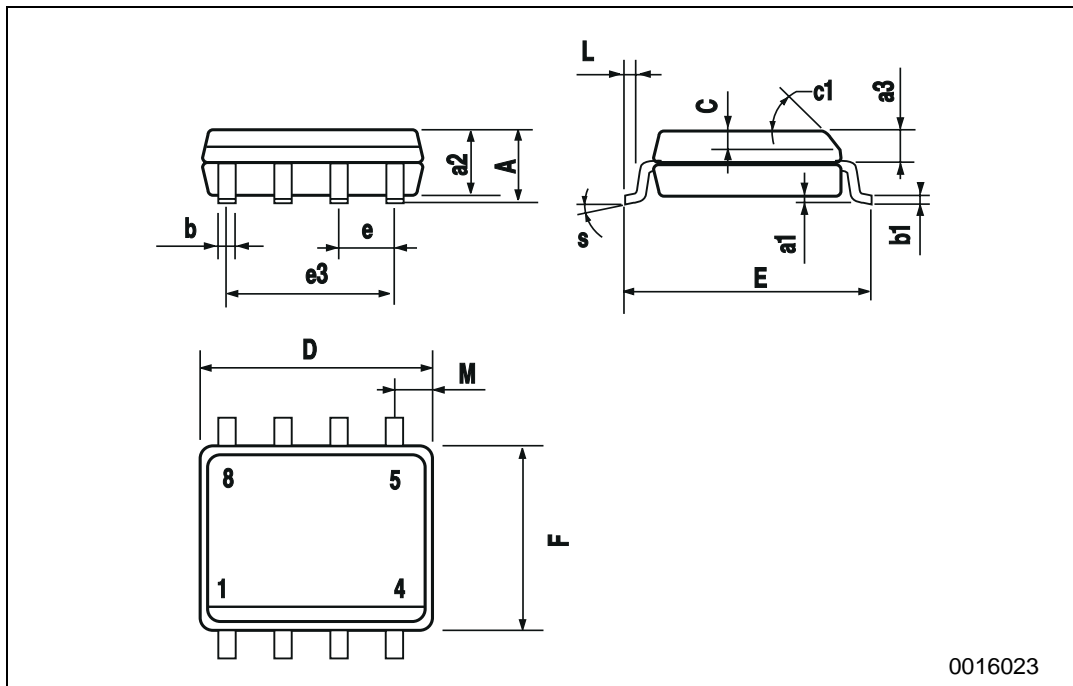


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



SO-8 MECHANICAL DATA

| DIM. | mm | | | inch | | |
|------|-----------|------|------|-------|-------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| A | | | 1.75 | | | 0.068 |
| a1 | 0.1 | | 0.25 | 0.003 | | 0.009 |
| a2 | | | 1.65 | | | 0.064 |
| a3 | 0.65 | | 0.85 | 0.025 | | 0.033 |
| b | 0.35 | | 0.48 | 0.013 | | 0.018 |
| b1 | 0.19 | | 0.25 | 0.007 | | 0.010 |
| C | 0.25 | | 0.5 | 0.010 | | 0.019 |
| c1 | 45 (typ.) | | | | | |
| D | 4.8 | | 5.0 | 0.188 | | 0.196 |
| E | 5.8 | | 6.2 | 0.228 | | 0.244 |
| e | | 1.27 | | | 0.050 | |
| e3 | | 3.81 | | | 0.150 | |
| F | 3.8 | | 4.0 | 0.14 | | 0.157 |
| L | 0.4 | | 1.27 | 0.015 | | 0.050 |
| M | | | 0.6 | | | 0.023 |
| S | 8 (max.) | | | | | |



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